

Amendments to the Claims

Listing of Claims:

Claims 10-12 (canceled)

Claim 13 (new) A method for forming an embedded resistor comprising the steps of:
depositing a thin film cermet material comprising $M_xSi_yO_z$;

where $M = W$ or Ta

said deposition onto a substrate is performed by co-sputtering of two targets: a
first target of W or Ta and a second target of SiO_2 ;

wherein sputtering of said SiO_2 target is r.f. sputtering; and,

deposition of the film on a substrate includes the steps of utilizing r.f. and d.c. magnetron
sputtering with argon gas; and controlling the resistivity and TCR of the thin film cermet material
by varying the sputtering power and pressure to obtain R_s and TCR values in accordance with the
following table:

R_s (ohms/Square)	TCR (ppm/C)	Pressure (mTorr)	Power (kW)
250	≤ -200	10	2.0
400	≤ -220	14	1.0
800	≤ -260	14	0.4
1500	≤ -400	18	0.4

Claim 14 (new) The invention according to claim 13 wherein said thin film cermet
material is approximately 1000 angstroms thick.